



IMPORTANT NOTICE

10 December 2015

1. Global joint venture starts operations as WeEn Semiconductors

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Thank you for your cooperation and understanding,

WeEn Semiconductors





ACTT12X-800CT

AC Thyristor Triac power switch

12 September 2014

Product data sheet

1. General description

Planar passivated AC Thyristor Triac power switch in a SOT186A (TO-220F) "full pack" plastic package with self-protective capabilities against low and high energy transients. This triac will commute the full RMS current at the maximum rated junction temperature ($T_{j(max)} = 150\text{ °C}$) without the aid of a snubber. It is used in applications where "high junction operating temperature capability" is required.

2. Features and benefits

- Clamping structure ensuring safe high over-voltage withstand capability
- High junction operating temperature capability
- Full cycle AC conduction
- Isolated mounting base package
- Less sensitive gate for high noise immunity
- Over-voltage withstand capability to IEC 61000-4-5
- Pin compatible with standard triacs
- Planar passivated for voltage ruggedness and reliability
- Safe clamping capability for low energy over-voltage transients
- Self-protective turn-on during high energy voltage transients
- Triggering in three quadrants only
- Very high immunity to false turn-on by dV/dt

3. Applications

- AC fan, pump and compressor controls
- Highly inductive, resistive and safety loads
- Large and small appliances (White Goods)
- Reversing induction motor controls
- Applications subject to high temperature

4. Quick reference data

Table 1. Quick reference data

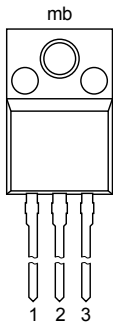
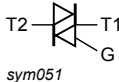
| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|-----------|--------------------------------------|---|-----|-----|-----|------|
| V_{DRM} | repetitive peak off-state voltage | | - | - | 800 | V |
| I_{TSM} | non-repetitive peak on-state current | full sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 20\text{ ms}$; Fig. 4 ; Fig. 5 | - | - | 120 | A |
| T_j | junction temperature | | - | - | 150 | °C |



| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|--------------------------------|---------------------------------------|--|-----|-----|-----|------------------|
| $I_{T(RMS)}$ | RMS on-state current | full sine wave; $T_h \leq 83\text{ }^\circ\text{C}$; Fig. 1 ; Fig. 2 ; Fig. 3 | - | - | 12 | A |
| V_{PP} | peak pulse voltage | $T_j = 25\text{ }^\circ\text{C}$; non-repetitive, off-state; Fig. 6 | - | - | 2 | kV |
| Static characteristics | | | | | | |
| I_{GT} | gate trigger current | $V_D = 12\text{ V}$; $I_T = 100\text{ mA}$; LD+ G+; $T_j = 25\text{ }^\circ\text{C}$; Fig. 8 | - | - | 35 | mA |
| | | $V_D = 12\text{ V}$; $I_T = 100\text{ mA}$; LD+ G-; $T_j = 25\text{ }^\circ\text{C}$; Fig. 8 | - | - | 35 | mA |
| | | $V_D = 12\text{ V}$; $I_T = 100\text{ mA}$; LD- G-; $T_j = 25\text{ }^\circ\text{C}$; Fig. 8 | - | - | 35 | mA |
| V_{CL} | clamping voltage | $I_{CL} = 0.1\text{ mA}$; $t_p = 1\text{ ms}$; $T_j = 25\text{ }^\circ\text{C}$ | 850 | - | - | V |
| Dynamic characteristics | | | | | | |
| dV_D/dt | rate of rise of off-state voltage | $V_{DM} = 536\text{ V}$; $T_j = 150\text{ }^\circ\text{C}$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; gate open circuit | 500 | - | - | V/ μs |
| di_{com}/dt | rate of change of commutating current | $V_D = 400\text{ V}$; $T_j = 150\text{ }^\circ\text{C}$; $I_{T(RMS)} = 12\text{ A}$; $dV_{com}/dt = 20\text{ V}/\mu\text{s}$; (snubberless condition); gate open circuit | 5 | - | - | A/ms |

5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------------------|--|---|
| 1 | T1 | main terminal 1 |  <p>TO-220F (SOT186A)</p> |  <p>sym051</p> |
| 2 | T2 | main terminal 2 | | |
| 3 | G | gate | | |
| mb | n.c. | mounting base; isolated | | |

6. Ordering information

Table 3. Ordering information

| Type number | Package | | |
|---------------|---------|---|---------|
| | Name | Description | Version |
| ACTT12X-800CT | TO-220F | plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack" | SOT186A |

7. Marking

Table 4. Marking codes

| Type number | Marking code |
|---------------|---------------|
| ACTT12X-800CT | ACTT12X-800CT |

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|--------------|--------------------------------------|--|-----|-----|------------------------|
| V_{DRM} | repetitive peak off-state voltage | | - | 800 | V |
| $I_{T(RMS)}$ | RMS on-state current | full sine wave; $T_h \leq 83\text{ }^\circ\text{C}$; Fig. 1 ; Fig. 2 ; Fig. 3 | - | 12 | A |
| I_{TSM} | non-repetitive peak on-state current | full sine wave; $T_{j(\text{init})} = 25\text{ }^\circ\text{C}$; $t_p = 20\text{ ms}$; Fig. 4 ; Fig. 5 | - | 120 | A |
| | | full sine wave; $T_{j(\text{init})} = 25\text{ }^\circ\text{C}$; $t_p = 16.7\text{ ms}$ | - | 132 | A |
| I^2t | I^2t for fusing | $t_p = 10\text{ ms}$; sine-wave pulse | - | 72 | A^2s |
| di_T/dt | rate of rise of on-state current | $I_T = 12\text{ A}$; $I_G = 0.2\text{ A}$; $di_G/dt = 0.2\text{ A}/\mu\text{s}$ | - | 100 | $\text{A}/\mu\text{s}$ |
| I_{GM} | peak gate current | $t = 20\text{ }\mu\text{s}$ | - | 2 | A |
| P_{GM} | peak gate power | | - | 5 | W |
| $P_{G(AV)}$ | average gate power | over any 20 ms period | - | 0.5 | W |
| T_{stg} | storage temperature | | -40 | 150 | $^\circ\text{C}$ |
| T_j | junction temperature | | - | 150 | $^\circ\text{C}$ |
| V_{PP} | peak pulse voltage | $T_j = 25\text{ }^\circ\text{C}$; non-repetitive, off-state; Fig. 6 | - | 2 | kV |

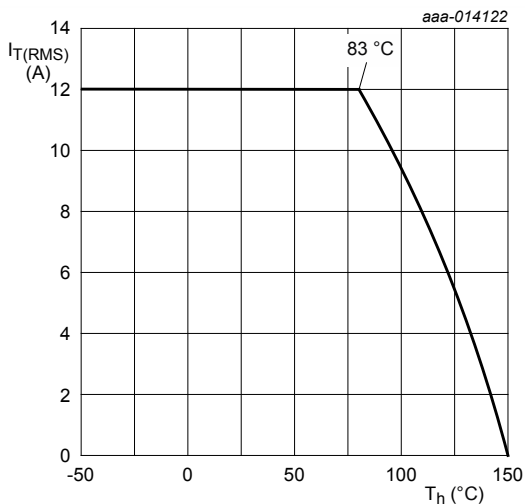
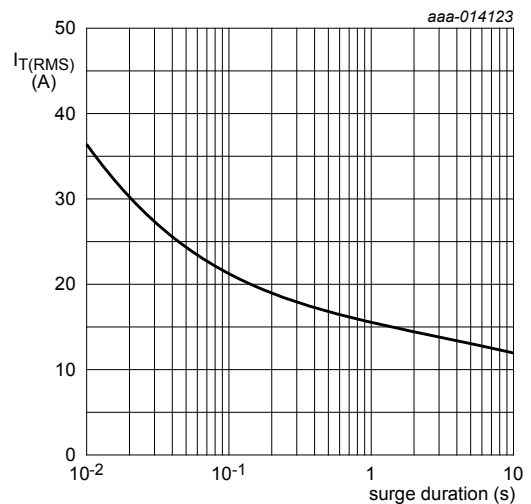


Fig. 1. RMS on-state current as a function of heatsink temperature; maximum values



$f = 50\text{ Hz}$; $T_h = 83\text{ }^\circ\text{C}$

Fig. 2. RMS on-state current as a function of surge duration; maximum values

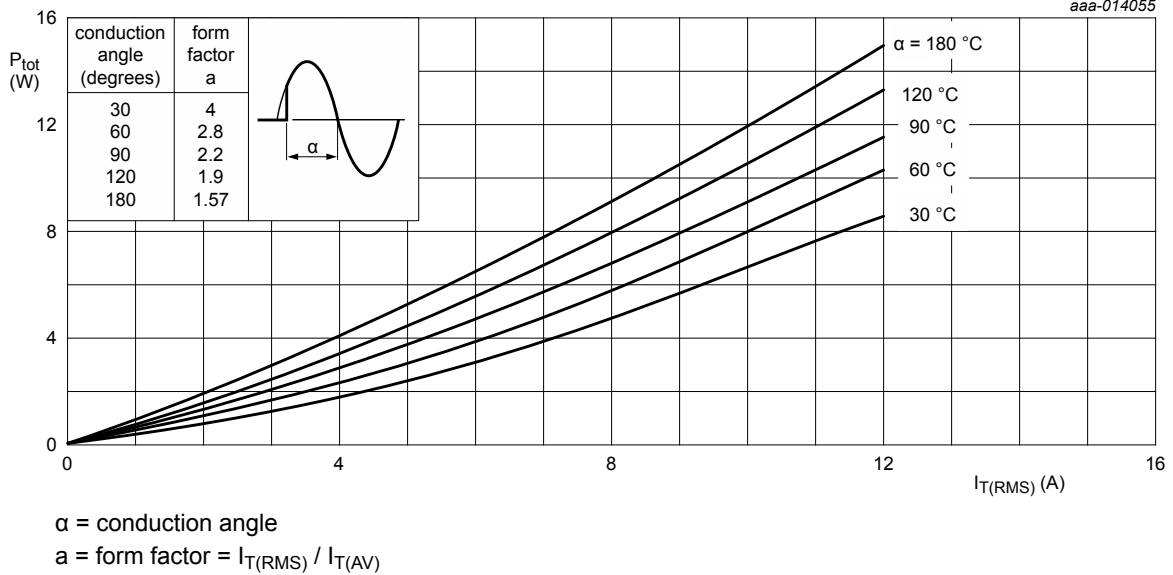


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

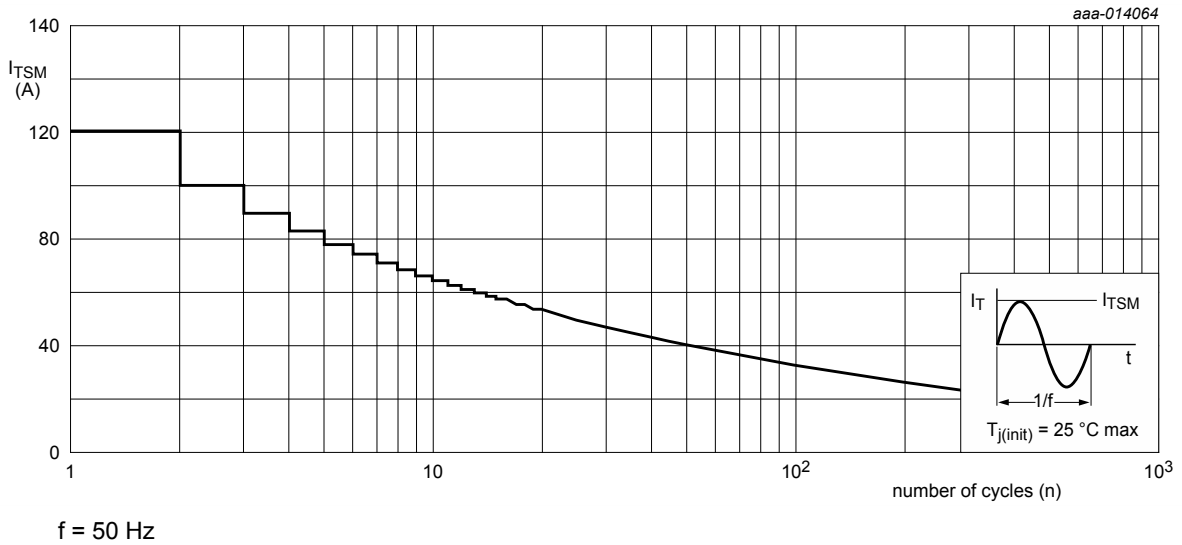


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

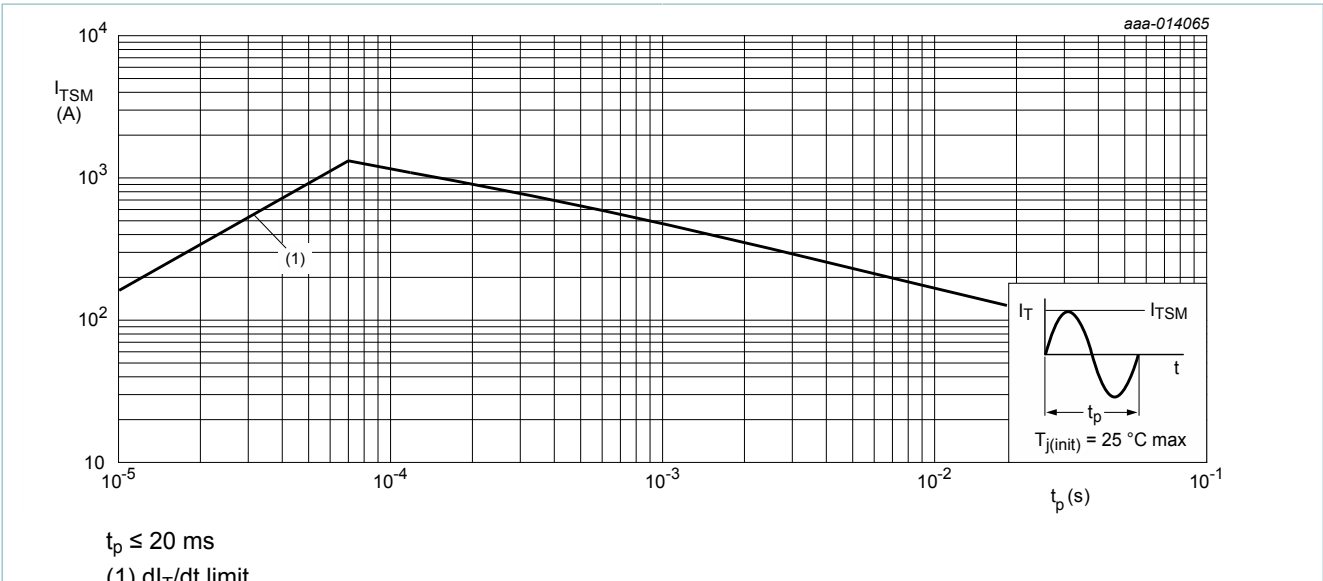


Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values

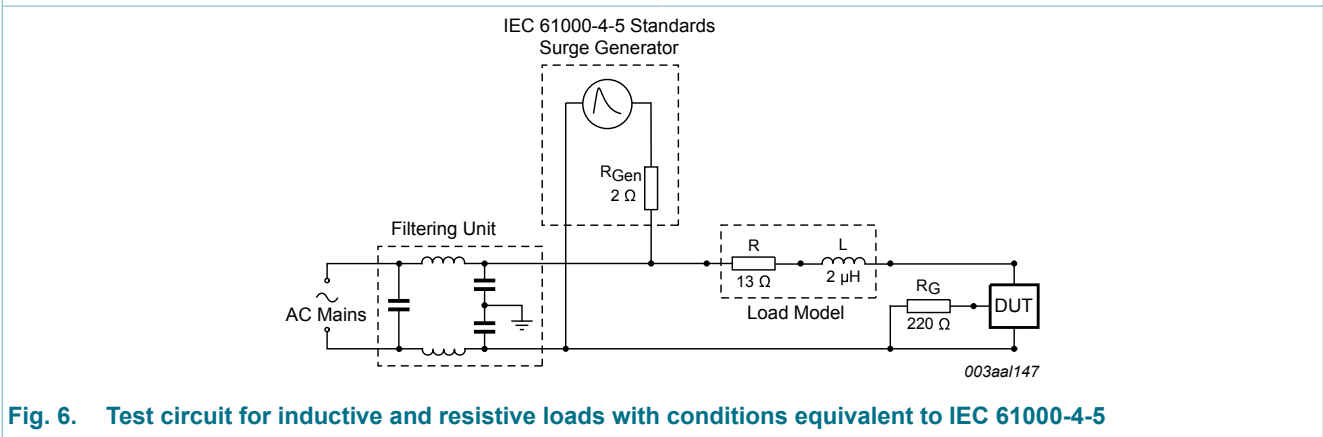


Fig. 6. Test circuit for inductive and resistive loads with conditions equivalent to IEC 61000-4-5

9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|---------------|--|--|-----|-----|-----|------|
| $R_{th(j-h)}$ | thermal resistance from junction to heatsink | full cycle; with heatsink compound; Fig. 7 | - | - | 4.5 | K/W |
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | in free air | - | 55 | - | K/W |

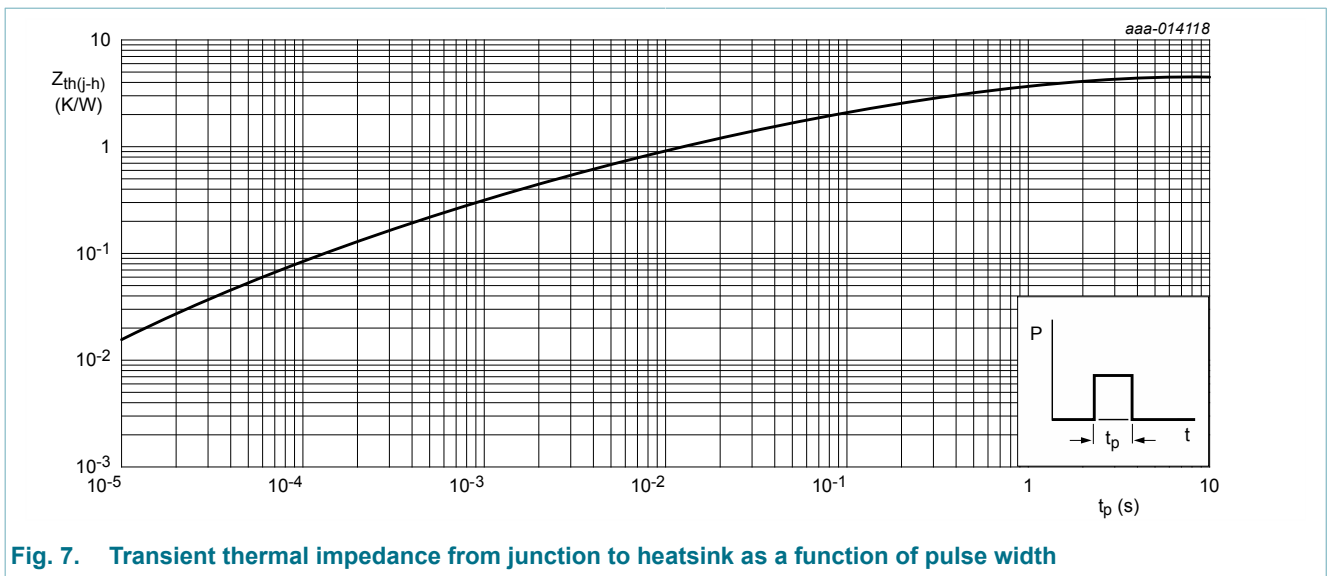


Fig. 7. Transient thermal impedance from junction to heatsink as a function of pulse width

10. Isolation characteristics

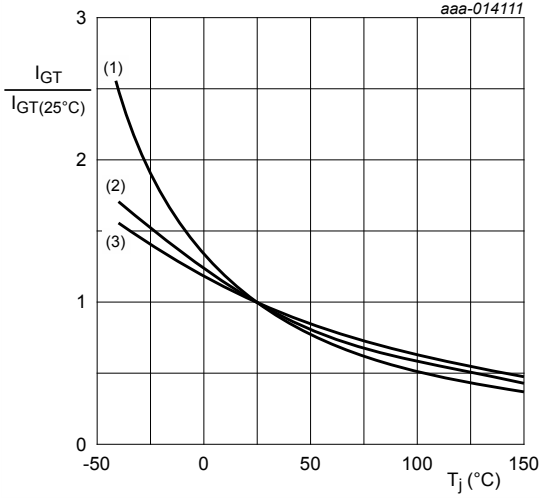
Table 7. Isolation characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|-----------------|-----------------------|--|-----|-----|------|------|
| $V_{isol(RMS)}$ | RMS isolation voltage | 50 Hz ≤ f ≤ 60 Hz; RH ≤ 65% RH; $T_h = 25\text{ °C}$; from all terminals to external heatsink; sinusoidal waveform; clean and dust free | - | - | 2500 | V |
| C_{isol} | isolation capacitance | f = 1 MHz; $T_h = 25\text{ °C}$; from main terminal 2 to external heatsink | - | 10 | - | pF |

11. Characteristics

Table 8. Characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|--------------------------------|---------------------------------------|--|-----|------|-----|------|
| Static characteristics | | | | | | |
| I _{GT} | gate trigger current | V _D = 12 V; I _T = 100 mA; LD+ G+; T _j = 25 °C; Fig. 8 | - | - | 35 | mA |
| | | V _D = 12 V; I _T = 100 mA; LD+ G-; T _j = 25 °C; Fig. 8 | - | - | 35 | mA |
| | | V _D = 12 V; I _T = 100 mA; LD- G-; T _j = 25 °C; Fig. 8 | - | - | 35 | mA |
| I _L | latching current | V _D = 12 V; I _G = 100 mA; LD+ G+; T _j = 25 °C; Fig. 9 | - | - | 50 | mA |
| | | V _D = 12 V; I _G = 100 mA; LD+ G-; T _j = 25 °C; Fig. 9 | - | - | 70 | mA |
| | | V _D = 12 V; I _G = 100 mA; LD- G-; T _j = 25 °C; Fig. 9 | - | - | 50 | mA |
| I _H | holding current | V _D = 12 V; T _j = 25 °C; Fig. 10 | - | - | 50 | mA |
| V _T | on-state voltage | I _T = 17 A; T _j = 25 °C; Fig. 11 | - | 1.25 | 1.5 | V |
| V _{GT} | gate trigger voltage | V _D = 12 V; I _T = 100 mA; T _j = 25 °C; Fig. 12 | - | 0.8 | 1 | V |
| | | V _D = 400 V; I _T = 100 mA; T _j = 150 °C; Fig. 12 | 0.2 | 0.45 | - | V |
| I _D | off-state current | V _D = 800 V; T _j = 25 °C | - | - | 10 | μA |
| | | V _D = 800 V; T _j = 150 °C | - | - | 0.5 | mA |
| V _{CL} | clamping voltage | I _{CL} = 0.1 mA; t _p = 1 ms; T _j = 25 °C | 850 | - | - | V |
| Dynamic characteristics | | | | | | |
| dV _D /dt | rate of rise of off-state voltage | V _{DM} = 536 V; T _j = 150 °C; (V _{DM} = 67% of V _{DRM}); exponential waveform; gate open circuit | 500 | - | - | V/μs |
| di _{com} /dt | rate of change of commutating current | V _D = 400 V; T _j = 150 °C; I _{T(RMS)} = 12 A; dV _{com} /dt = 20 V/μs; (snubberless condition); gate open circuit | 5 | - | - | A/ms |



- (1) LD- G-
- (2) LD+ G+
- (3) LD+ G-

Fig. 8. Normalized gate trigger current as a function of junction temperature

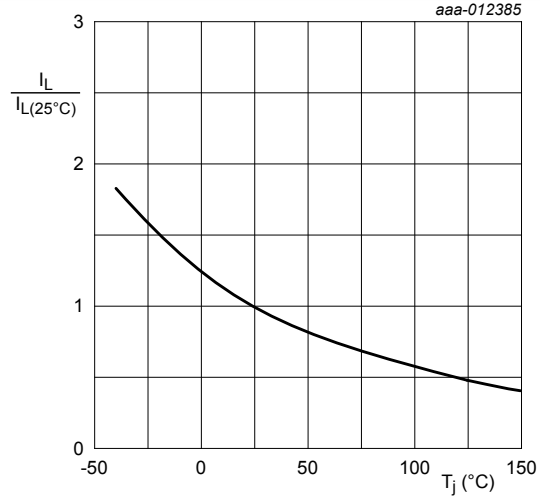


Fig. 9. Normalized latching current as a function of junction temperature

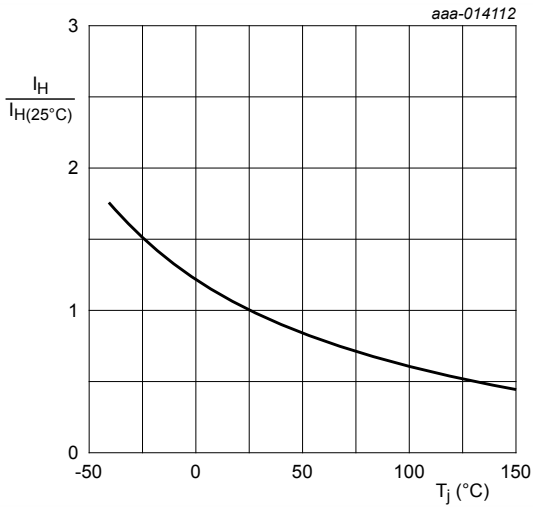
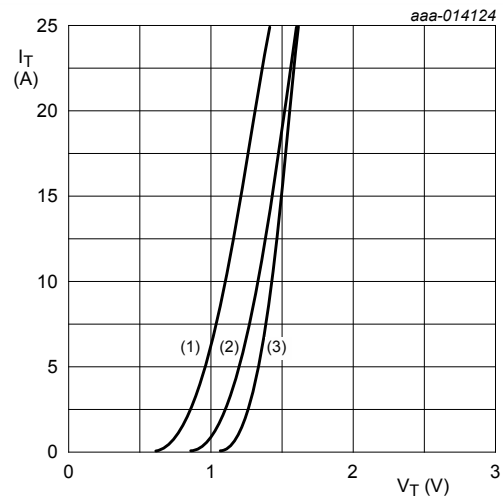


Fig. 10. Normalized holding current as a function of junction temperature



$V_o = 0.989\text{ V}$; $R_s = 0.029\ \Omega$

- (1) $T_j = 150^\circ\text{C}$; typical values
- (2) $T_j = 150^\circ\text{C}$; maximum values
- (3) $T_j = 25^\circ\text{C}$; maximum values

Fig. 11. On-state current as a function of on-state voltage

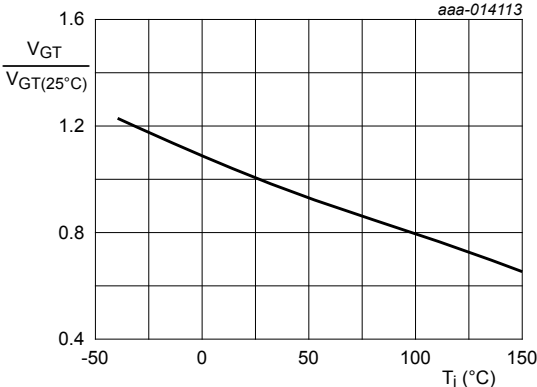


Fig. 12. Normalized gate trigger voltage as a function of junction temperature

12. Package outline

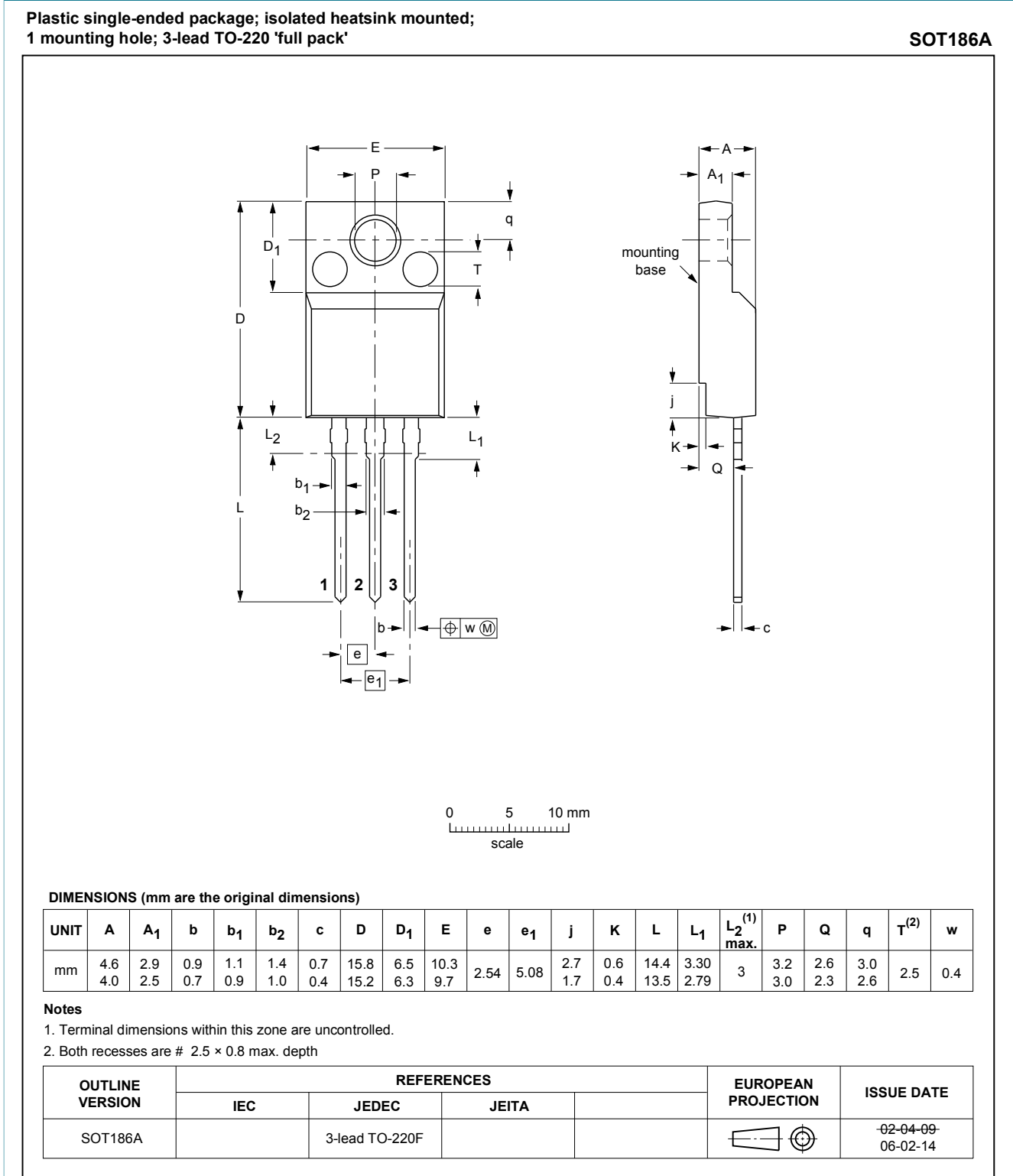


Fig. 13. Package outline TO-220F (SOT186A)

13. Legal information

13.1 Data sheet status

| Document status [1][2] | Product status [3] | Definition |
|--------------------------------|--------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
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